

CORRECTION

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Correction: Atomic-scale structure and thermoelectric properties in medium-entropy PbSnTeSe alloy

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Correction for 'Atomic-scale structure and thermoelectric properties in medium-entropy PbSnTeSe alloy' by Shuwei Zhang *et al.*, *J. Mater. Chem. A*, 2024, <https://doi.org/10.1039/D4TA05952B>.

The authors regret that some of the alloy chemical formulae in the published article contained unintended errors. The details are as described below.

The formula 'PbSn_{0.98}Cu_{0.04}PbSe' should have been written as 'PbSn_{0.98}Cu_{0.04}TeSe'. This error was present in the following locations:

- Three instances in the Abstract, in the sentences beginning 'Furthermore, through progressive optimisation...' and 'Consequently, a ZT value...'
- Two instances in the final sentence of the Introduction, which begins 'Consequently, the carrier mobility...'
- One instance in the Conclusions, in the sentence beginning 'Subsequently, by introducing additional Sn vacancies...'

Additionally, the formula 'PbSn_{0.98}Cu_{0.04}TeSe' was incorrectly used in place of 'PbSnCu_{0.04}TeSe' in one sentence in Section 3.5, which begins 'Meanwhile, a p-n convert can be observed...'

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.



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